

N-channel 30 V 1.3 mΩ logic level MOSFET in I2PAK

2 April 2014

Product data sheet

1. General description

Logic level N-channel MOSFET in I2PAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

2. Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for logic level gate drive sources

3. Applications

- DC-to-DC converters
- Load switiching
- Motor control
- Server power supplies

4. Quick reference data

Table 1. Q	uick reference data						
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	30	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 2</u>	[1]	-	-	120	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	338	W
Tj	junction temperature			-55	-	175	°C
Static chara	cteristics						
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 12	[2]	-	1.1	1.3	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 100 °C; Fig. 13		-	1.5	1.8	mΩ
Dynamic cha	aracteristics						
Q _{GD}	gate-drain charge	V_{GS} = 4.5 V; I _D = 75 A; V _{DS} = 15 V;		-	37	-	nC
Q _{G(tot)}	total gate charge	<u>Fig. 14; Fig. 15</u>		-	118	-	nC

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Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
Avalanche ruggedness							
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	$\label{eq:VGS} \begin{array}{l} V_{GS} \texttt{=} 10 \; V; \; T_{j(\text{init})} \texttt{=} 25 \; ^{\circ}\text{C}; \; I_{D} \texttt{=} 120 \; A; \\ V_{sup} \texttt{\leq} 30 \; V; \; R_{GS} \texttt{=} 50 \; \Omega; \; \text{unclamped} \end{array}$		-	-	1.9	J

[1] Continuous current is limited by package.

[2] Measured 3 mm from package.

5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	D	drain		
3	S	source		G LIT A
mb	D	mounting base; connected to drain	1 2 3 12PAK (SOT226)	mbb076 S

6. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
PSMN1R1-30EL	12PAK	plastic single-ended package (I2PAK); TO-262	SOT226			

7. Marking

Table 4. Marking codes	
Type number	Marking code
PSMN1R1-30EL	PSMN1R1-30EL

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	30	V
V _{DGR}	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	30	V
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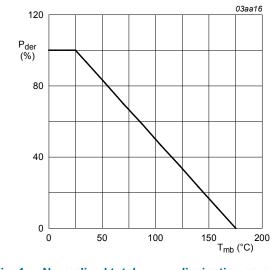
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Symbol	Parameter	Conditions		Min	Max	Unit
V _{GS}	gate-source voltage			-20	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	338	W
I _D	drain current	V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 2</u>	[1]	-	120	Α
		V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	120	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$; Fig. 3		-	1609	А
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T _{sld(M)}	peak soldering temperature			-	260	°C
Source-dra	in diode					
I _S	source current	T _{mb} = 25 °C	[1]	-	120	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$		-	1609	А
Avalanche	ruggedness	,				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; T _{j(init)} = 25 °C; I _D = 120 A; V _{sup} ≤ 30 V; R _{GS} = 50 Ω; unclamped		-	1.9	J

[1] Continuous current is limited by package.





$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

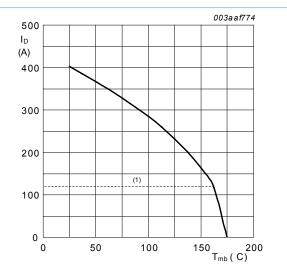
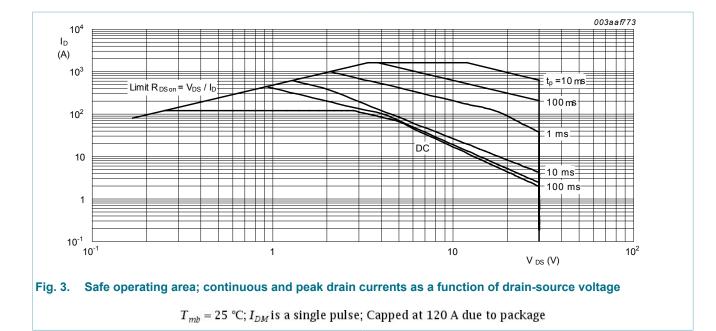


Fig. 2. Continuous drain current as a function of mounting base temperature.

 $V_{GS} \ge 10 \text{ V}; \quad (1) \text{ Capped at } 120 \text{ A due to package}$

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9. Thermal characteristics

Table 6. Tl	hermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. <u>4</u>	-	0.22	0.44	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	Vertical in free air	-	60	-	K/W

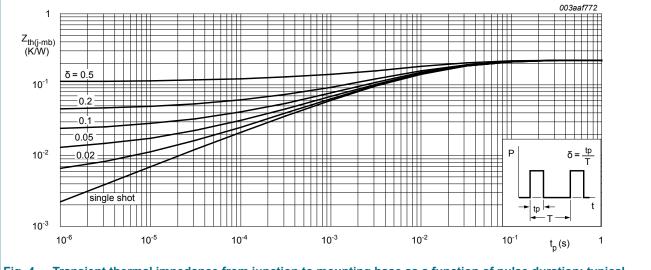


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical values

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10. Characteristics

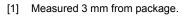
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static chara	acteristics	1					
V _{(BR)DSS}	drain-source	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C		30	-	-	V
	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C		27	-	-	V
V _{GS(th)}	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; Fig. 10; Fig. 11		1.3	1.7	2.15	V
		I _D = 2 mA; V _{DS} = V _{GS} ; T _j = 175 °C; Fig. 11		0.5	-	-	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C; Fig. 11		-	-	2.5	V
I _{DSS}	drain leakage current	V _{DS} = 30 V; V _{GS} = 0 V; T _j = 25 °C		-	0.02	10	μA
		V _{DS} = 30 V; V _{GS} = 0 V; T _j = 175 °C		-	250	500	μA
I _{GSS}	gate leakage current	V _{GS} = 16 V; V _{DS} = 0 V; T _j = 25 °C		-	10	100	nA
		V _{GS} = -16 V; V _{DS} = 0 V; T _j = 25 °C		-	10	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 12	[1]	-	1.1	1.3	mΩ
		V _{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C; Fig. 12		-	1.2	1.6	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; Fig. 13; Fig. 12		-	2.1	2.5	mΩ
		V_{GS} = 10 V; I _D = 25 A; T _j = 100 °C; Fig. 13		-	1.5	1.8	mΩ
R _G	gate resistance	f = 1 MHz		-	1.1	-	Ω
Dynamic ch	naracteristics	·					
Q _{G(tot)}	total gate charge	I _D = 75 A; V _{DS} = 15 V; V _{GS} = 10 V; Fig. 14; Fig. 15		-	243	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V};$ Fig. 14; Fig. 15		-	222	-	nC
		I_D = 75 A; V_{DS} = 15 V; V_{GS} = 4.5 V;		-	118	-	nC
Q _{GS}	gate-source charge	Fig. 14; Fig. 15		-	39	-	nC
Q _{GS(th)}	pre-threshold gate- source charge			-	22	-	nC
Q _{GS(th-pl)}	post-threshold gate- source charge			-	17	-	nC
Q _{GD}	gate-drain charge			-	37	-	nC
V _{GS(pl)}	gate-source plateau voltage	V _{DS} = 15 V; <u>Fig. 14;</u> <u>Fig. 15</u>		-	2.8	-	V

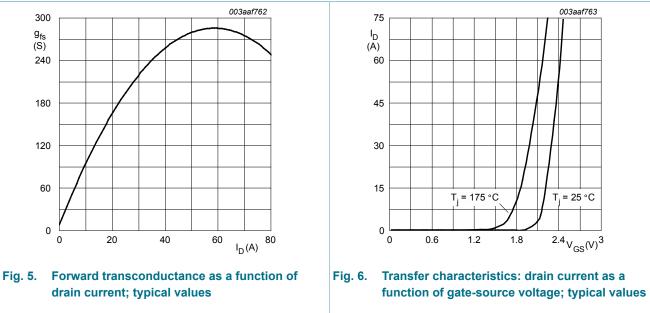
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Symbol	Parameter	Conditions	Mi	n Typ	Мах	Unit
C _{iss}	input capacitance	V_{DS} = 15 V; V_{GS} = 0 V; f = 1 MHz;	-	14850	-	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 16</u>	-	2799	-	pF
C _{rss}	reverse transfer capacitance	-	-	1215	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 15 V; R_L = 0.2 Ω ; V_{GS} = 4.5 V; $R_{G(ext)}$ = 5 Ω ; I_D = 75 A; T_j = 25 °C	-	95	-	ns
t _r	rise time		-	213	-	ns
t _{d(off)}	turn-off delay time		-	199	-	ns
t _f	fall time		-	115	-	ns
Source-dra	in diode	1		I		
V _{SD}	source-drain voltage	I_{S} = 25 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 17</u>	-	0.8	1.2	V
t _{rr}	reverse recovery time	$I_{\rm S}$ = 25 A; dI _S /dt = -100 A/µs; V _{GS} = 0 V; V _{DS} = 15 V	-	67	-	ns
Q _r	recovered charge		-	123	-	nC



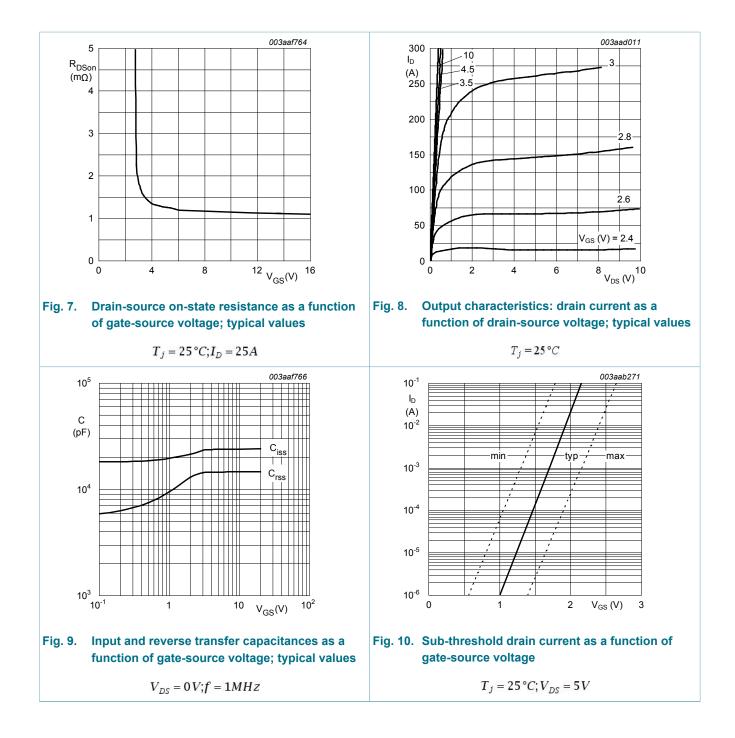


 $T_j = 25 \,^{\circ}C; V_{DS} = 15V$



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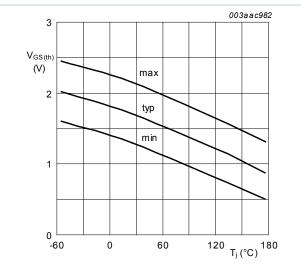
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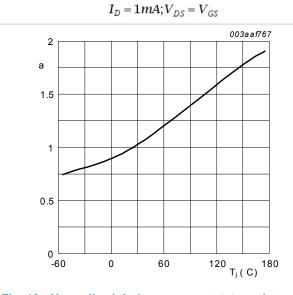
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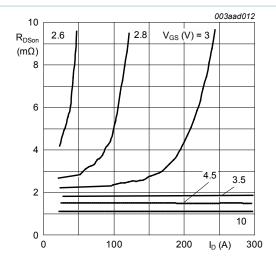








 $a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$





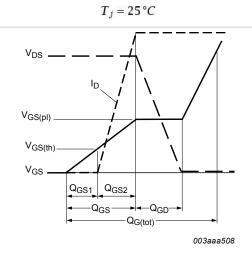
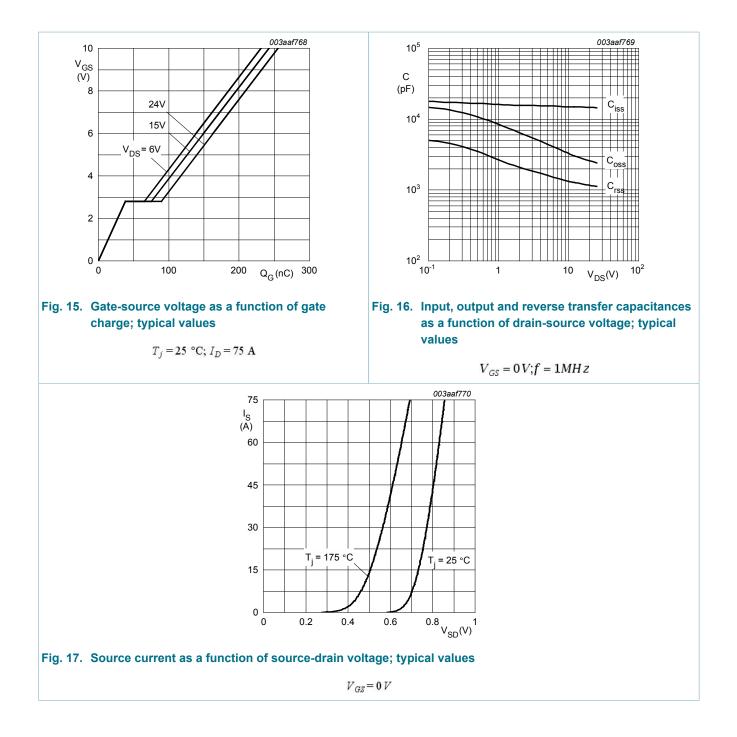


Fig. 14. Gate charge waveform definitions

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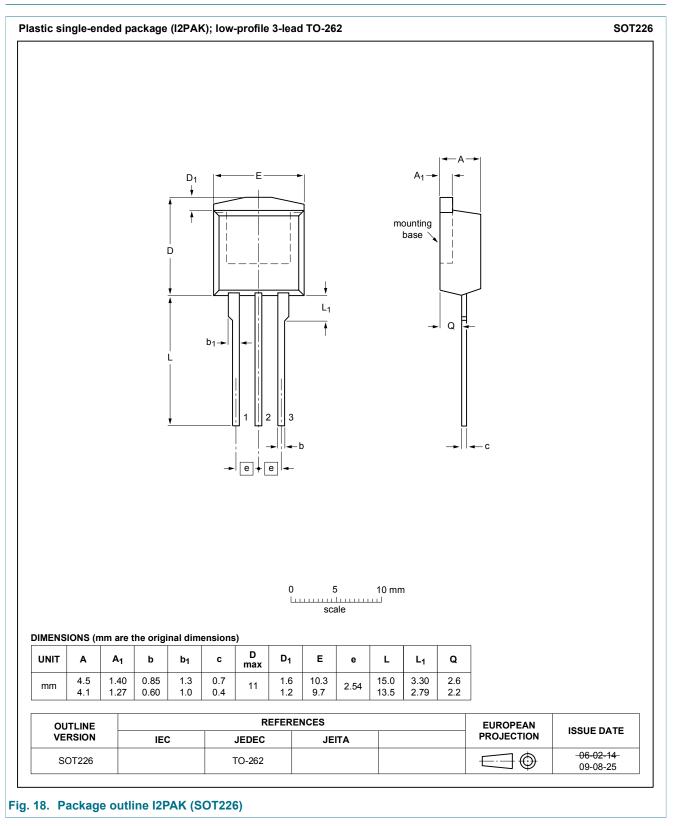
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11. Package outline



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12. Legal information

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